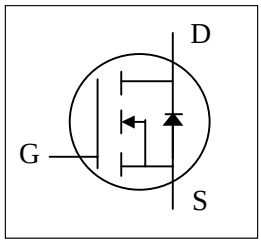
XP10NA1R5TL

Halogen-Free Product

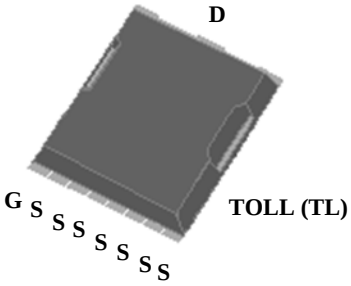
N-CHANNEL ENHANCEMENT MODE

POWER MOSFET

- **100% R_g & UIS Test**
- **Simple Drive Requirement**
- **Ultra Low On-resistance**
- **RoHS Compliant & Halogen-Free**



BV_{DSS}	100V
$R_{DS(ON)}$	1.5mΩ



Description

XP10NA1R5 series are innovative design and silicon process technology to achieve the lowest possible on-resistance and fast switching performance. It provides the designer with an extreme efficient device for use in a wide range of power applications.

The TOLL package is a perfect solution for high power density and high power efficiency application.

Absolute Maximum Ratings@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_C=25℃	Drain Current, V_{GS} @ 10V[4](Silicon Limited)	347	A
I_D@T_C=25℃	Drain Current, V_{GS} @ 10V[4]	300	A
I_D@T_C=100℃	Drain Current, V_{GS} @ 10V	245	A
I_{DM}	Pulsed Drain Current[1]	1200	A
P_D@T_C=25℃	Total Power Dissipation	333	W
P_D@T_A=25℃	Total Power Dissipation[3]	3.75	W
E_{AS}	Single Pulse Avalanche Energy[5]	500	mJ
T_{STG}	Storage Temperature Range	-55 to 175	℃
T_J	Operating Junction Temperature Range	-55 to 175	℃

Thermal Data

Symbol	Parameter	Value	Units
Rthj-c	Maximum Thermal Resistance, Junction-case	0.45	℃/W
Rthj-a	Maximum Thermal Resistance, Junction-ambient (PCB mount)[3]	40	℃/W

Electrical Characteristics@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=250uA	100	-	-	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10V, I_D=100A	-	-	1.5	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250uA	2	-	4	V
g_{fs}	Forward Transconductance	V_{DS}=5V, I_D=100A	-	195	-	S
I_{DSS}	Drain-Source Leakage Current	V_{DS}=80V, V_{GS}=0V	-	-	25	uA
I_{GSS}	Gate-Source Leakage	V_{GS}= ±20V, V_{DS}=0V	-	-	±0.1	uA
Q_g	Total Gate Charge	I_D=100A	-	190	304	nC
Q_{gs}	Gate-Source Charge	V_{DS}=50V	-	53	-	nC
Q_{gd}	Gate-Drain ("Miller") Charge	V_{GS}=10V	-	60	-	nC
$t_{d(on)}$	Turn-on Delay Time	V_{DS}=50V	-	40	-	ns
t_r	Rise Time	I_D=100A	-	320	-	ns
$t_{d(off)}$	Turn-off Delay Time	R_G=3.3Ω	-	95	-	ns
t_f	Fall Time	V_{GS}=10V	-	370	-	ns
C_{iss}	Input Capacitance	V_{GS}=0V	-	10600	16960	pF
C_{oss}	Output Capacitance	V_{DS}=80V	-	1600	-	pF
C_{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	45	-	pF
R_g	Gate Resistance	f=1.0MHz	-	1	2	Ω

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_{SD}	Forward On Voltage[2]	I_S=100A, V_{GS}=0V	-	-	1.3	V
t_{rr}	Reverse Recovery Time	I_S=100A, V_{GS}=0V	-	130	-	ns
Q_{rr}	Reverse Recovery Charge	dI/dt=100A/μs	-	290	-	nC

Notes:

1.Pulse width limited by Max. junction temperature.

2.Pulse test

3.Surface mounted on 1 in^2 copper pad of FR4 board

4.Package limitation current is 300A .

5.Starting T_j=25°C , V_{DD}=50V , L=0.1mH , R_G=25Ω

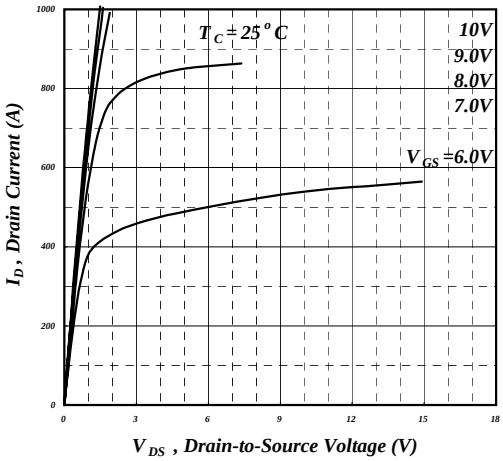


Fig 1. Typical Output Characteristics

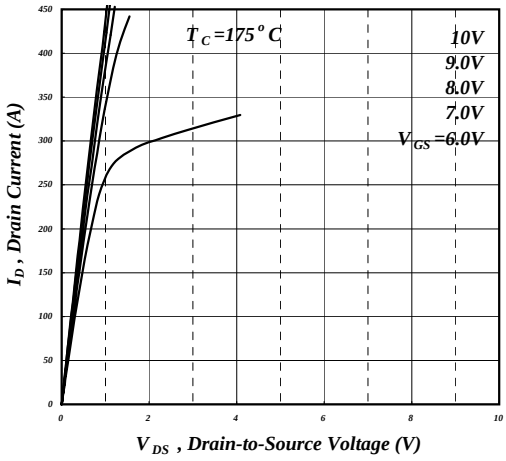


Fig 2. Typical Output Characteristics

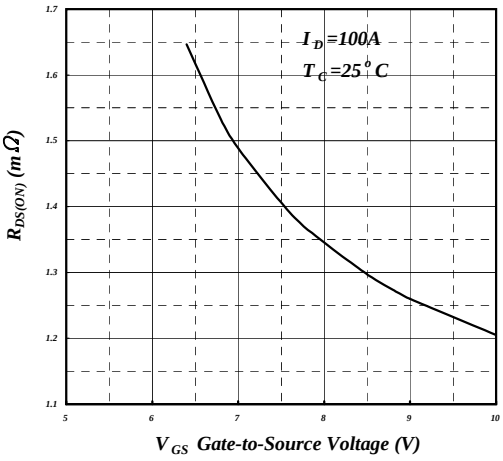


Fig 3. On-Resistance v.s. Gate Voltage

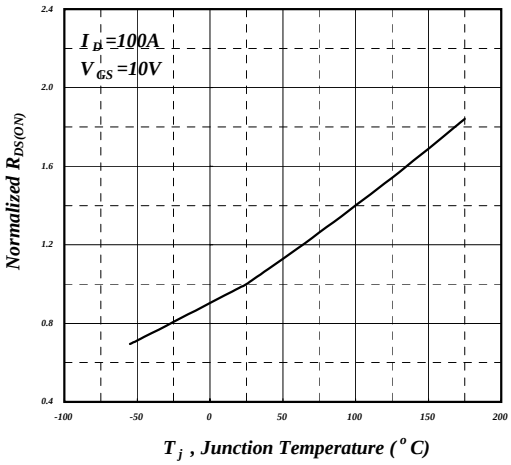


Fig 4. Normalized On-Resistance v.s. Junction Temperature

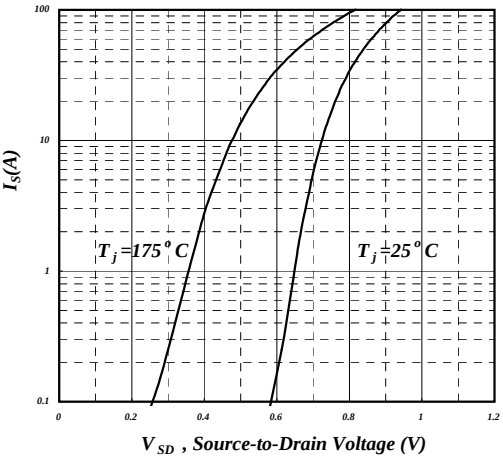


Fig 5. Forward Characteristic of Reverse Diode

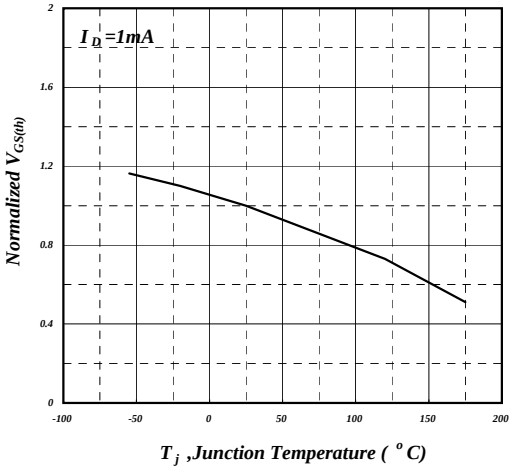


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

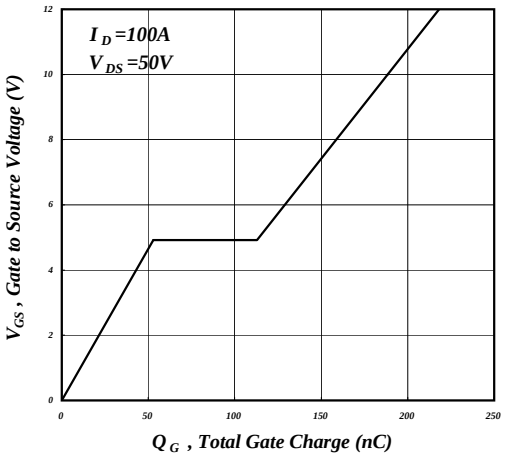


Fig 7. Gate Charge Characteristics

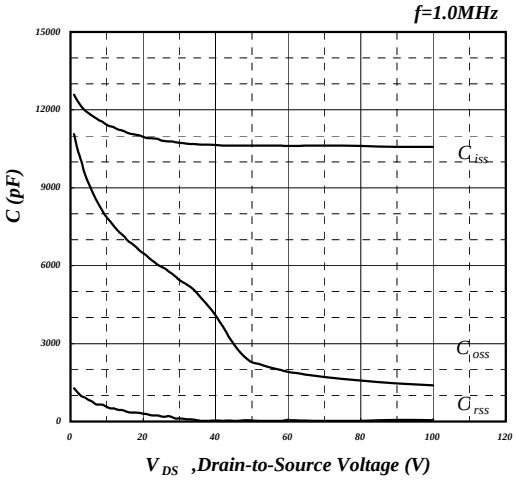


Fig 8. Typical Capacitance Characteristics

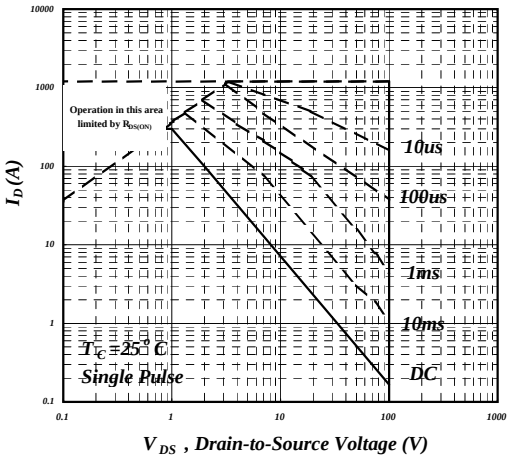


Fig 9. Maximum Safe Operating Area

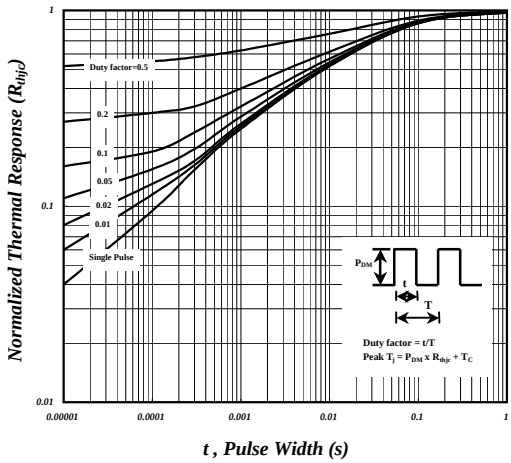


Fig 10. Effective Transient Thermal Impedance

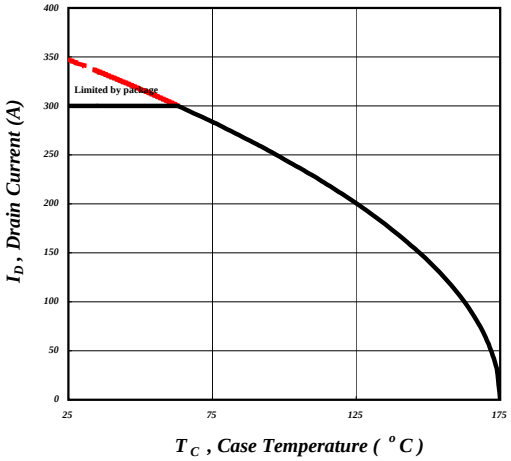


Fig 11. Drain Current v.s. Case Temperature

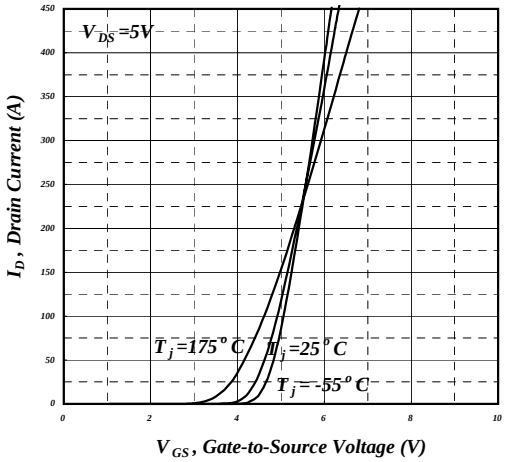


Fig 12. Transfer Characteristics

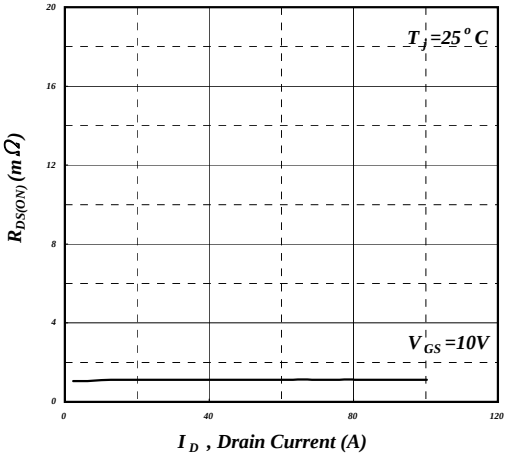


Fig 13. Typ. Drain-Source on State Resistance

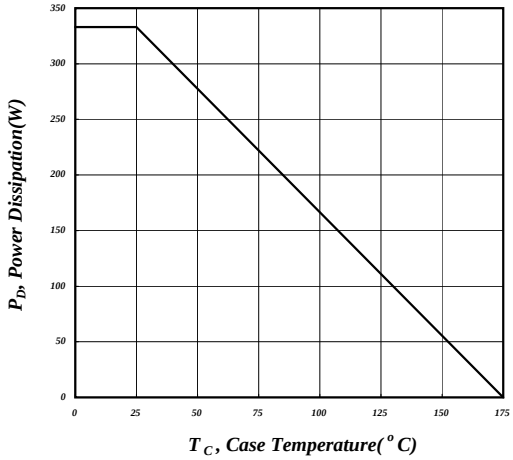


Fig 14. Total Power Dissipation